

In The Claims:

Claim 1. (original) An erasing method for a p-channel nitride read only memory, wherein the p-channel nitride read only memory has a control gate, a drain and a source, and formed in a n-well, the erasing method comprising:

applying a positive voltage to the control gate and a negative voltage to the drain;

floating the source; and

grounding the n-well.

Claim 2. (original) The erasing method of claim 1, wherein a voltage difference between the positive voltage applied to the control gate and the negative voltage to the drain is sufficient to trigger a band-to-band induced hot electron injection to erase the p-channel nitride read only memory.

Claim 3. (original) The erasing method of claim 1, wherein the voltage difference is not sufficient to open a channel of the p-channel nitride read only memory.

Claims 4-9 (canceled)